L Number	Hits	Search Text	DB	Time stamp
48	16	(((((memory adj device) and capacitor) and vertical adj3 transistor) and select$7 adj2 transistor) and adjacent near5 lines) and second adj3 lines	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 11:44
50	2	fuhrmann-D$7.in. and trench adj capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 11:46
52	3	fuhrmann-D$7.in. and select$8 adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 11:46
53	28201	(memory adj device) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 11:56
54	137	((memory adj device) and capacitor) and zigzag	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 11:57
55	10	(((memory adj device) and capacitor) and zigzag) and select$7 adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 12:21
51	2	"20040135190"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 13:21
49	21	fuhrmann-D$7.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 14:08
-	1	US20040022100A1	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/27 18:36
-	2	"20040022100"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/29 17:47
-	172710	memory adj device	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/29 17:48
-	1	2004-110827.NRAN. and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/29 17:48
-	590	((memory adj device) and capacitor) and vertical adj3 transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/29 17:49
-	98	(((memory adj device) and capacitor) and vertical adj3 transistor) and select$7 adj2 transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/29 17:50
-	48	((((memory adj device) and capacitor) and vertical adj3 transistor) and select$7 adj2 transistor) and adjacent near5 lines	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/29 17:50
-	10	(((((memory adj device) and capacitor) and vertical adj3 transistor) and select$7 adj2 transistor) and adjacent near5 lines) and first adj2 lines	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/29 17:51

-	8	((((((memory adj device) and capacitor) and vertical adj3 transistor) and select$7 adj2 transistor) and adjacent near5 lines) and first adj2 lines) and ((((((memory adj device) and capacitor) and vertical adj3 transistor) and select$7 adj2 transistor) and adjacent near5 lines) and second adj3 lines)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/29 17:54
-	6	(("5,691,934") or ("5,736,761") or ("6,118,683")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/29 17:56
-	6	6,448,600	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/29 17:55
-	3	5,691,934	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/29 17:56
-	10	5,736,761	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/29 17:56
-	3	6,118,683	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/29 17:56
-	22	6,448,600 or 5,691,934 or 5,736,761 or 6,118,683	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/29 17:57